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Description

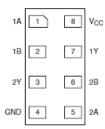
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G00 is a dual two input NAND gate. Both gates have push-pull outputs designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using $l_{\rm OFF}$. The $l_{\rm OFF}$ circuitry disables the output preventing damaging current backflow when the device is powered down. Each gate performs the positive Boolean function:

$$Y = \overline{A \bullet B}$$
 or $Y = \overline{A} + \overline{B}$

Pin Assignments

(Top View)



X2-DFN1210-8

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
 I_{CC} < 0.9µA
- Low Dynamic Power Consumption

 C_{PD} = 6 pF (Typical at 3.6V)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at V_{CC} = 3.0V
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

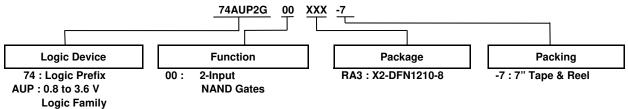
- Suited for Battery and Low Power Needs
- Wide Array of Products Such as:
 - Tablets. E-readers
 - Cell Phones, Personal Navigation/GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



2G : Dual Gate

Device	Package	7" Tape and	d Reel		
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP2G00RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

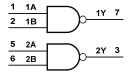
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram



Function Table

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L



Absolute Maximum Ratings (Note 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	50	mA
lok	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol	Pa	rameter	Min	Max	Unit
V _{CC}	Operating Voltage	_	0.8	3.6	٧
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	High Lavel Output Compant	V _{CC} = 1.4V	_	-1.7	
I _{OH}	V ₁ Input Voltage V _O Output Voltage DH High-Level Output Current Low-Level Output Current ΔV Input Transition Rise or Fall Rate	V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
	Lave Lavel Cutaut Cumant	V _{CC} = 1.4V	_	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
	Input Voltage O Output Voltage High-Level Output Current Low-Level Output Current Input Transition Rise or Fall Rate	V _{CC} = 2.3V	_	3.1	
	Output Voltage High-Level Output Current Low-Level Output Current AV Input Transition Rise or Fall Rate	V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommended values.

^{7.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely, forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics

Symbol	Parameter	Test Conditions	V _{CC}	T _A = -	+25°C	T _A = -40°C	C to +85°C	Unit
Symbol	Parameter	rest Conditions	V CC	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	_	
V	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	V
V _{IH}	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	V
		_	3.0V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 X V _{CC}	_	0.30 X V _{CC}	
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.35 X V _{CC}	_	0.35 X V _{CC}	V
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	V
		_	3.0V to 3.6V	_	0.9	_	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.1	_	V _{CC} – 0.1	_	
		I _{OH} = -1.1mA	1.1V	0.75 X V _{CC}	_	0.7 X V _{CC}	_	
		I _{OH} = -1.7mA	1.4V	1.11	_	1.03	_	
.,	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	_	1.3	_	V
V _{OH}	voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	_	V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	1
		I _{OH} = -2.7mA	01/	2.72	_	2.67	_	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	١,,
V _{OL}	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA		_	0.31	_	0.33	
		I _{OL} = 4mA	- 3V	_	0.44	_	0.45	
II	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
l _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0V	_	± 0.2	_	± 0.6	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μΑ
Δl _{CC}	Additional Supply Current	One Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	40	_	50	μΑ



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit
Syllibol	Faranietei	rest Conditions	V _{CC}	Min	Max	Offic
		_	0.8V to 1.65V	0.80 X V _{CC}		
V _{IH}	High Loyal Input Valtage	_	1.65V to 1.95V	0.70 X V _{CC}	_	V
VIH	High-Level Input Voltage Low-Level Input Voltage High-Level Output Voltage Low-Level Input Voltage Input Current Power Down Leakage Current	_	2.3V to 2.7V	1.6		V
		_	3.0V to 3.6V	2.0	_	
		_	0.8V to 1.65V	_	0.25 X V _{CC}	
V_{IL}	Low-Level Input Voltage	_	1.65V to 1.95V		0.30 X V _{CC}	V
V IL	Low Level input voltage	_	2.3V to 2.7V	_	0.7	_
		_	3.0V to 3.6V		0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_	
		$I_{OH} = -1.1$ mA	1.1V	0.6 X V _{CC}	_	
		I _{OH} = -1.7mA	1.4V	0.93		
.,	V _{OH} High-Level Output Voltage	I _{OH} = -1.9mA	1.65V	1.17	_	٧
VOH		I _{OH} = -2.3mA	2.21/	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	21/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
.,	Lava Lava Harrist Walterna	I _{OL} = 1.9mA	1.65V	_	0.39	
V_{OL}	Low-Level input voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
	OL Low-Level Input Voltage	I _{OL} = 2.7mA	01/	_	0.36	
		I _{OL} = 4mA	3V	_	0.50	
l _l	Input Current	A or B Input, V_1 = GND to 3.6V	0V to 3.6V	_	± 0.75	μA
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA
Δlcc	Additional Supply Current	Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μΑ

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Tes Condi		V _{CC}	Тур	Unit
				0.8V	5.1	
				1.2V ± 0.1V	5.2	
	Power Dissipation	f = 1N	ЛHz	1.5V ± 0.1V	5.2	Ī
C_{pd}	Capacitance	No Lo	oad	1.8V ± 0.15V	5.5	pF
				2.5V ± 0.2V	5.7	
				3.3V ± 0.3V	6.0	
C _i	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF
θ _{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	X2-DFN1210-8 (Note 9)		395	°C/W
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L=5pF, See Figure 1

Parameter From	то	V	1	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		
Parameter	Input	OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	20.1	_	_	_	_	_	
			1.2V ± 0.1V	2.5	5.3	12.1	2.1	13.4	2.1	14.9	
4.	۸		1.5V ± 0.1V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	no
t _{pd}	Α	I	1.8V ± 0.15V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
			2.5V ± 0.2V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	
			3.3V ± 0.3V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	

C_L= 10pF, See Figure 1

Parameter	From	то	V _{CC}	Т	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C	to +125°C	Unit
Parameter	Input	OUTPUT		Min	Тур	Max	Min	Max	Min	Max	Oiiit
			V8.0	_	24.2	_	_	_	_	_	
		1.2V ± 0.1V	2.4	6.1	14.3	2.2	15.8	2.2	17.5		
	^	V	1.5V ± 0.1V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	
t _{pd}	Α	ı	1.8V ± 0.15V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	ns
			2.5V ± 0.2V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	
			$3.3V \pm 0.3V$	1.3	2.8	4.3	1.2	4.9	1.2	5.4	

C_L = 15pF, See Figure 1

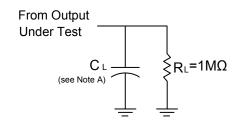
Parameter	From	то	Vcc	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C	Unit		
Parameter	Input	OUTPUT		Min	Тур	Max	Min	Max	Min	Max	Oilit
			V8.0	_	28.2	_	_	_	_	_	
			1.2V ± 0.1V	3.4	6.9	16.3	3.1	20.3	3.1	20.5	
	^	V	1.5V ± 0.1V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	
t _{pd}	Α	T T	1.8V ± 0.15V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	ns
			2.5V ± 0.2V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	
		$3.3V \pm 0.3V$	1.4	3.2	4.9	1.3	5.7	1.3	6.3		

C_L = 30pF, See Figure 1

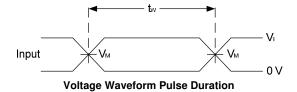
Parameter	From	то	V	T	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C	Unit	
Parameter	Input	OUTPUT	V _{CC}	Min	Тур	Min	Min	Max	Min	Max	Oilit
			V8.0	_	40.0	_	_	_	_	_	
			1.2V ± 0.1V	4.6	9.2	22.1	4.1	27.8	4.1	28.0	
	۸		1.5V ± 0.1V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	no
lpd	t _{pd} A Y	ī	1.8V ± 0.15V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	ns
			2.5V ± 0.2V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.0	4.3	6.5	1.8	7.6	1.8	8.4	

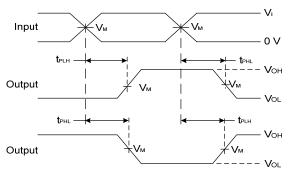


Parameter Measurement Information



Vcc	Inputs		V	0
	VI	t _r /t _f	V _M	C _L
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8

(Top View)

 $\underline{XX}\,:\,$ Identification Code

<u>Y</u> : Year : 0~9

 $\overline{\underline{W}}$: week: A~Z: 1~26 week

a~z: 27-52 week

Identification Code

ΑT

Package

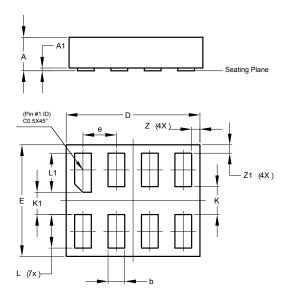
X2-DFN1210-8

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

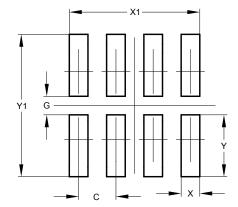
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

Part Number

74AUP2G00RA3-7



X2-DFN1210-8					
Dim	Min	Max	Тур		
Α	-	0.35	0.30		
A 1	0	0.03	0.02		
b	0.10	0.20	0.15		
D	1.15	1.25	1.20		
Е	0.95	1.05	1.00		
е	-	-	0.30		
K	-	-	0.25		
K1	-	-	0.20		
L	0.25	0.35	0.30		
L1	0.30	0.40	0.35		
Z	0.050	0.100	0.075		
Z 1	0.050	0.100	0.075		
All Dimensions in mm					



Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Υ	0.500	
Y1	1.150	



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 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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